

Form PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 5649-805DV	Serial No. To Be Assigned				
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicants: Kang-Wook Park	Filing Date: Concurrently Herewith				
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Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
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DF	2	6,030,882	02/2000	Hong	438	433	
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DF	25	Pruijnbom et al., <i>18 ps ECL-Gate Delay in Laterally Scaled 30 GHz Bipolar Transistors</i> , IEDM, 1994, pp. 825-828					
DF	26	Uchino, <i>15-ps ECL/74-GHz f_T Si Bipolar Technology</i> , IEDM, 1993, pp. 67-70					
DF	27	Ugajin et al., <i>Very-High f_T and f_{max} Silicon Bipolar Transistors Using Ultra-High-Performance Super Self-Aligned Process Technology for Low-Energy and Ultra-High-Speed LSI's</i> , IEDM, 1995, pp. 735-738					
DF	28	Wolf, S., <i>Silicon Processing for the VLSI Era Volume 2: Process Integration</i> , Sunset Beach, CA, 1990, pp. 52, 510-512					
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DF	30	Yoshino et al., <i>A 62.8 GHz f_{max} LP-CVD Epitaxially Grown Silicon Base Bipolar Transistor With Extremely High Early Voltage of 85.7V</i> , Symposium on VLSI Technology Digest of Technical Papers, 1995, pp. 131-132					

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Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.